

DEFECT-RELATED PHOTOLUMINESCENCE OF C₆₀ THIN FILMS: EFFECT OF STRAINS AND TEMPERATURE

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The results of studies of low temperature photoluminescence of C₆₀ thin films fabricated by the deposition in vacuum on the heated up substrates (NaCl crystalline plate, mica) are presented. The films structures was analyzed by standard transmission high energy electron diffraction (THEED) technique. The structure analysis showed that the structure of films depend on a deposition rate, substrate temperature, and film thickness. Earlier [1 - 4] the supposition was put forward that structural defects play the important role for shaping of C₆₀ photoluminescence spectrum. For clearing up of a nature of defects, researches of the effects of temperature and strains on photoluminescence spectra were conducted. The structural defects originated both as because of difference of C₆₀ thin film thermal expansion coefficients and because of a bending of C₆₀ thin film deposited on mica.

Influence of strains was observed on the 1.76 and 1.71 eV defect-related photoluminescence bands (see Figure). The features of a temperature behavior of the 1.76 and 1.79 eV photoluminescence bands are also investigated. Processes of defects formation and electronic excitations trapping are discussed.

References.

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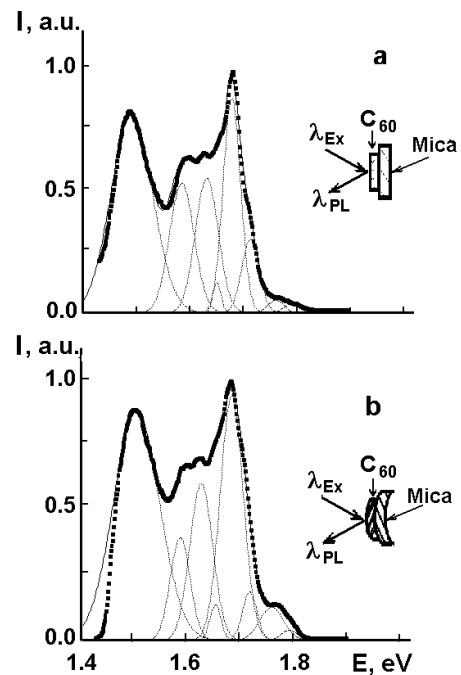


Figure. Photoluminescence spectra of C₆₀ thin epitaxial film of 90 nm thickness deposited on mica:
a - plane specimen, **b** - bent specimen.
I is a photoluminescence intensity in arbitrary units, **E** is a light energy in eV. Photoluminescence was excited by the 2.27 eV radiation at 5K, the curves were fitted by Gaussians.